

Appl. No. 10/777,608

Attorney Docket No. 10808-119

I. Amendments to the Specification

Please replace paragraph [0004] with the following amended paragraph:

[0004] A process for planarizing the ILD, referred to as a chemical mechanical polishing (CMP) process, includes using a polishing tool, a pad and a slurry in a sequence of steps to planarize a surface of the wafer and/or to remove undesired materials from the surface of the wafer. The polishing pad is coupled with the polishing tool. The pad is applied to the surface of the wafer. The polishing pad applies the polishing slurry against the surface of the wafer. The pad and slurry are traversed across the surface of the wafer, generally by rotating the pad with respect to the surface of the wafer. The slurry may include polishing agents or chemical abrasives that remove undesired materials ~~[[form]]~~ from the wafer and ~~[[forma]]~~ form a planar surface.

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